



#### P-CHANNEL ENHANCEMENT MODE MOSFET

#### **Product Summary**

V	Р	ID		
V <sub>(BR)DSS</sub>	R <sub>DS(on) max</sub>	$T_A = 25^{\circ}C$		
201/	$45m\Omega @ V_{GS} = -10V$	-4.3A		
-30V	$65m\Omega @ V_{GS} = -4.5V$	-3.3A		

### Description

This new generation MOSFET has been designed to minimize the onstate resistance ( $R_{DS(on)}$ ) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

# Applications

- General Purpose Interfacing Switch
- Power Management Functions
- Analog Switch

#### Features

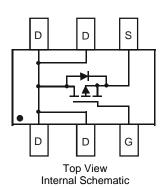
- Low Gate Threshold Voltage
- Low On-Resistance
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

## **Mechanical Data**

- Case: SOT26
- Case Material Molded Plastic, "Green" Molding Compound. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Weight: 0.008 grams (approximate)



Top View



### Ordering Information (Note 4)

Part Number	Qualification	Case	Packaging
DMP3056LDM-7	Commercial	SOT26	3000/Tape & Reel
DMP3056LDMQ-7	Automotive	SOT26	3000/Tape & Reel

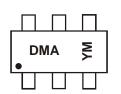
Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

2. See http://www.diodes.com for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com.

# **Marking Information**



DMA = Product Type Marking Code YM = Date Code Marking Y = Year (ex: V = 2008) M = Month (ex: 9 = September)

#### Date Code Key

Year	2008		2009	2010		2011	2012		2013	2014		2015
Code	V		W	Х		Y	Z		А	В		С
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



### **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units	
Drain-Source Voltage		V <sub>DSS</sub>	-30	V	
Gate-Source Voltage		V <sub>GSS</sub>	±20	V	
Continuous Drain Current (Note 6) V <sub>GS</sub> = 10V	Steady State	T <sub>A</sub> = +25°C	I <sub>D</sub>	-4.3	А
	t < 10s	T <sub>A</sub> = +25°C	ID	-5.8	А
Maximum Continuous Body Diode Forward Curr	ent (Note 6)	Is	-2.3	А	
Pulsed Drain Current (10µs pulse, duty cycle = 1	%)	IDM	-13	А	

# **Thermal Characteristics**

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)	T <sub>A</sub> = +25°C	PD	1.25	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{ heta JA}$	100	°C/W
Total Power Dissipation (Note 6)	T <sub>A</sub> = +25°C	PD	1.5	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{ heta JA}$	86	°C/W
Thermal Resistance, Junction to Case		$R_{ ext{ heta}JC}$	15.6	·C/W
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to 150	°C

### Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

	Symbol			1			
		Min	Тур	Max	Unit	Test Condition	
STATIC PARAMETERS (Note 7)							
Drain-Source Breakdown Voltage		-30			V	$V_{GS} = 0V, I_D = -250\mu A$	
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	IDSS	_		-1	μΑ	$V_{GS} = 0V, V_{DS} = -30V$	
Gate-Body Leakage Current			_	±100 ±800	nA		
Gate Threshold Voltage	V <sub>GS(th)</sub>	-1.0		-2.1	V	$V_{GS} = V_{DS}, I_D = -250 \mu A$	
Static Drain-Source On-Resistance				45 65	mΩ	$V_{GS} = -10V, I_D = -5A$ $V_{GS} = -4.5V, I_D = -4.2A$	
Forward Transconductance	<b>g</b> fs	—	8		S	$V_{DS} = -10V, I_D = -4.3A$	
Diode Forward Voltage		_		-1.2	V	$V_{GS} = 0V, I_{S} = -1.7A$	
DYNAMIC PARAMETERS (Note 8)							
Input Capacitance	Ciss	_	948	_	pF	V <sub>GS</sub> = 0V, V <sub>DS</sub> = -25V, f = 1.0MHz	
Output Capacitance	Coss	_	105		рF		
Reverse Transfer Capacitance	Crss	_	100		pF		
SWITCHING CHARACTERISTICS (Note 8)						·	
Total Gate Charge			10.1	_	nC	$V_{DS} = -15V, V_{GS} = -4.5V, I_D = -6A$	
	$Q_G$	_	21.1			$\label{eq:VDS} \begin{split} V_{DS} &= -15 V, \ V_{GS} = -10 V, \\ I_D &= -6 A \end{split}$	
Gate-Source Charge	Q <sub>GS</sub>	_	2.8		nC		
Gate-Drain Charge	Q <sub>GD</sub>		3.2				
Gate Resistance	Rq		13.15		Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$	
Turn-On Delay Time	t <sub>d(on)</sub>	_	10.2				
Rise Time		_	6.6	_		$V_{DS} = -15V, V_{GS} = -10V,$	
Turn-Off Delay Time	t <sub>d(off)</sub>	_	50.1		ns	$I_D = -1A, R_G = 6.0\Omega$	
Fall Time	t <sub>f</sub>		22.3		1		

5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper pad

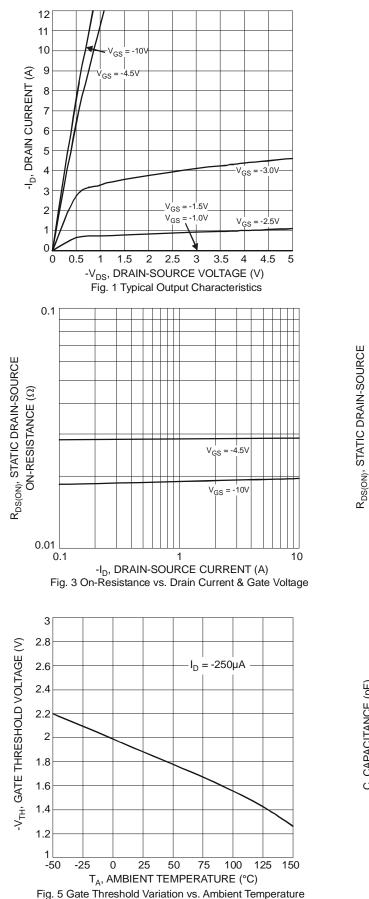
7. Short duration pulse test used to minimize self-heating effect.

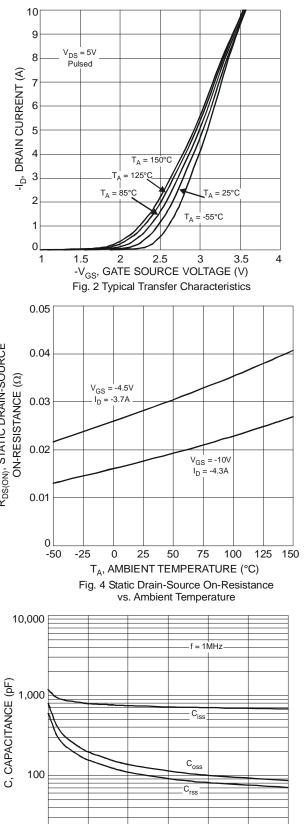
8. Guaranteed by design. Not subject to product testing.

Notes:

# DMP3056LDM



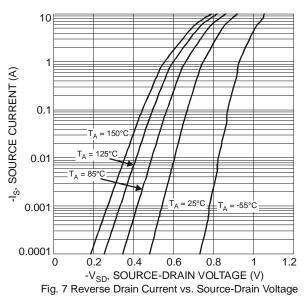


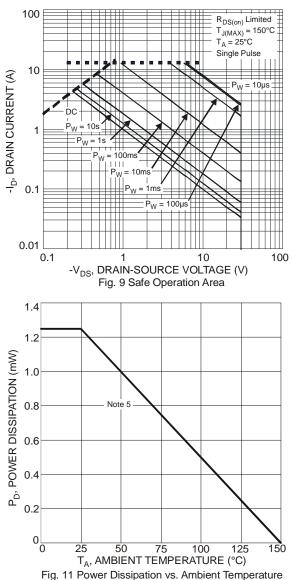


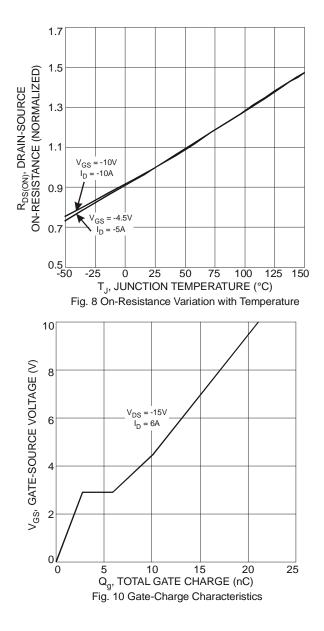
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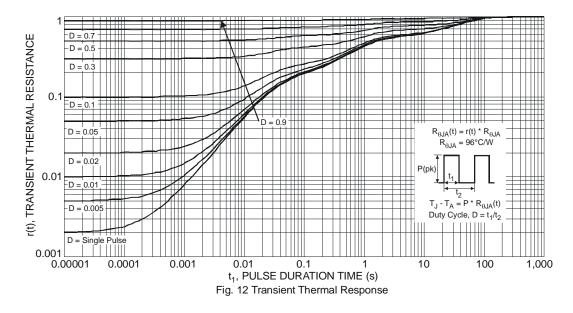






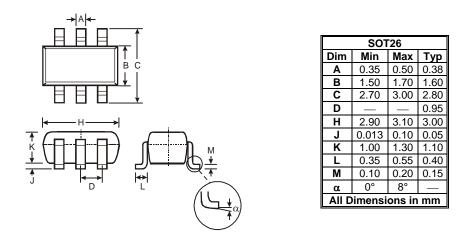






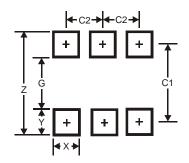
# **Package Outline Dimensions**

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



### Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	3.20
G	1.60
Х	0.55
Y	0.80
C1	2.40
C2	0.95



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